30V N-Channel NexFET™ Power MOSFET

FEATURES

- Optimized for 5V Gate Drive
- Ultra Low Q_g and Q_{gd}
- Low Thermal Resistance
- Pb Free
- RoHS Compliant
- Halogen Free
- SON 2-mm × 2-mm Plastic Package

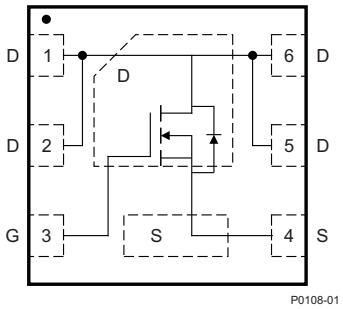
APPLICATIONS

- DC-DC Converters
- Battery and Load Management Applications

DESCRIPTION

The NexFET power MOSFET has been designed to minimize losses in power conversion applications and optimized for 5V gate drive applications. The 2-mm × 2-mm SON offers excellent thermal performance for the size of the package.

Top View



PRODUCT SUMMARY

V_{DS}	Drain to Source Voltage	30		V
Q_g	Gate Charge Total (4.5V)	2.1		nC
Q_{gd}	Gate Charge Gate to Drain	0.4		nC
$R_{DS(on)}$	Drain to Source On Resistance	V_{GS} = 3V	31	mΩ
		V_{GS} = 4.5V	26	mΩ
		V_{GS} = 8V	24	mΩ
$V_{GS(th)}$	Threshold Voltage	1.3		V

ORDERING INFORMATION

Device	Package	Media	Qty	Ship
CSD17313Q2	SON 2-mm × 2-mm Plastic Package	13-Inch Reel	3000	Tape and Reel

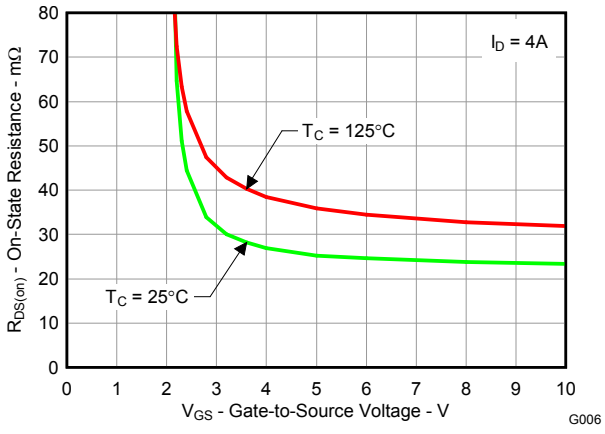
ABSOLUTE MAXIMUM RATINGS

T_A = 25°C unless otherwise stated		VALUE	UNIT
V_{DS}	Drain to Source Voltage	30	V
V_{GS}	Gate to Source Voltage	+10 / –8	V
I_D	Continuous Drain Current, T_C = 25°C	5	A
	Continuous Drain Current(1)	5	A
I_{DM}	Pulsed Drain Current, T_A = 25°C(2)	20	A
P_D	Power Dissipation	2.3	W
T_J, T_{STG}	Operating Junction and Storage Temperature Range	–55 to 150	°C
E_{AS}	Avalanche Energy, Single Pulse, I_D = 19A, L = 0.1mH, R_G = 25Ω	18	mJ

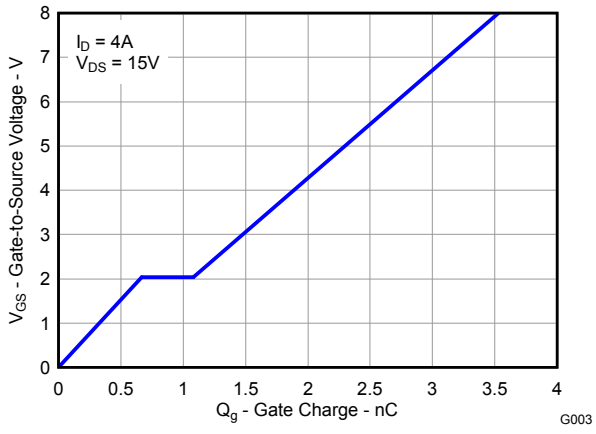
(1) Package Limited

(2) Pulse duration ≤300μs, duty cycle ≤2%

$R_{DS(on)}$ vs V_{GS}



GATE CHARGE



These devices have limited built-in ESD protection. The leads should be shorted together or the device placed in conductive foam during storage or handling to prevent electrostatic damage to the MOS gates.

ELECTRICAL CHARACTERISTICS

(T_A = 25°C unless otherwise stated)

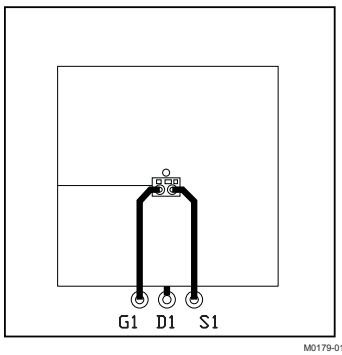
PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT
Static Characteristics						
BV_{DSS}	Drain to Source Voltage	V_{GS} = 0V, I_D = 250µA	30			V
I_{DSS}	Drain to Source Leakage	V_{GS} = 0V, V_{DS} = 24V			1	µA
I_{GSS}	Gate to Source Leakage	V_{DS} = 0V, V_{GS} = +10 / -8V			100	nA
$V_{GS(th)}$	Gate to Source Threshold Voltage	V_{DS} = V_{GS}, I_D = 250µA	0.9	1.3	1.8	V
$R_{DS(on)}$	Drain to Source On Resistance	V_{GS} = 3V, I_D = 4A		31	42	mΩ
		V_{GS} = 4.5V, I_D = 4A		26	32	mΩ
		V_{GS} = 8V, I_D = 4A		24	30	mΩ
g_{fs}	Transconductance	V_{DS} = 15V, I_D = 4A		16		S
Dynamic Characteristics						
C_{iss}	Input Capacitance	V_{GS} = 0V, V_{DS} = 15V, f = 1MHz		260	340	pF
C_{oss}	Output Capacitance			140	180	pF
C_{rss}	Reverse Transfer Capacitance			13	17	pF
R_G	Series Gate Resistance			1.3	2.6	Ω
Q_g	Gate Charge Total (4.5V)	V_{DS} = 15V, I_D = 4A		2.1	2.7	nC
Q_{gd}	Gate Charge – Gate to Drain			0.4		nC
Q_{gs}	Gate Charge Gate to Source			0.7		nC
$Q_{g(th)}$	Gate Charge at Vth			0.3		nC
Q_{oss}	Output Charge	V_{DS} = 13.5V, V_{GS} = 0V		3.8		nC
$t_{d(on)}$	Turn On Delay Time	V_{DS} = 15V, V_{GS} = 4.5V, I_D = 4A, R_G = 2Ω		2.8		ns
t_r	Rise Time			3.9		ns
$t_{d(off)}$	Turn Off Delay Time			4.2		ns
t_f	Fall Time			1.3		ns
Diode Characteristics						
V_{SD}	Diode Forward Voltage	I_{SD} = 4A, V_{GS} = 0V		0.85	1	V
Q_{rr}	Reverse Recovery Charge	V_{DD}= 13.5V, I_F = 4A, di/dt = 300A/µs		6.4		nC
t_{rr}	Reverse Recovery Time			12.9		ns

THERMAL CHARACTERISTICS

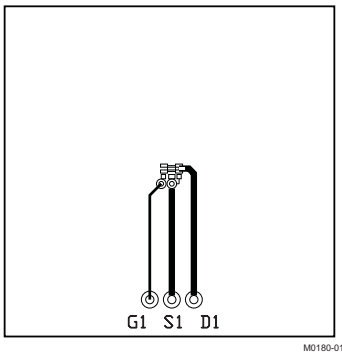
(T_A = 25°C unless otherwise stated)

PARAMETER		MIN	TYP	MAX	UNIT
$R_{\theta JC}$	Thermal Resistance Junction to Case(1)			7.4	°C/W
$R_{\theta JA}$	Thermal Resistance Junction to Ambient(1)(2)			67	°C/W

(1) $R_{\theta JC}$ is determined with the device mounted on a 1-inch^2 (6.45-cm^2), 2-oz. (0.071-mm thick) Cu pad on a 1.5-inch × 1.5-inch (3.81-cm × 3.81-cm), 0.06-inch (1.52-mm) thick FR4 PCB. $R_{\theta JC}$ is specified by design, whereas $R_{\theta JA}$ is determined by the user's board design.
(2) Device mounted on FR4 material with 1-inch^2 (6.45-cm^2), 2-oz. (0.071-mm thick) Cu.



Max $R_{\theta JA}$ = 67°C/W when mounted on 1 inch^2 (6.45 cm^2) of 2-oz. (0.071-mm thick) Cu.



Max $R_{\theta JA}$ = 228°C/W when mounted on a minimum pad area of 2-oz. (0.071-mm thick) Cu.

TYPICAL MOSFET CHARACTERISTICS

(T_A = 25°C unless otherwise stated)

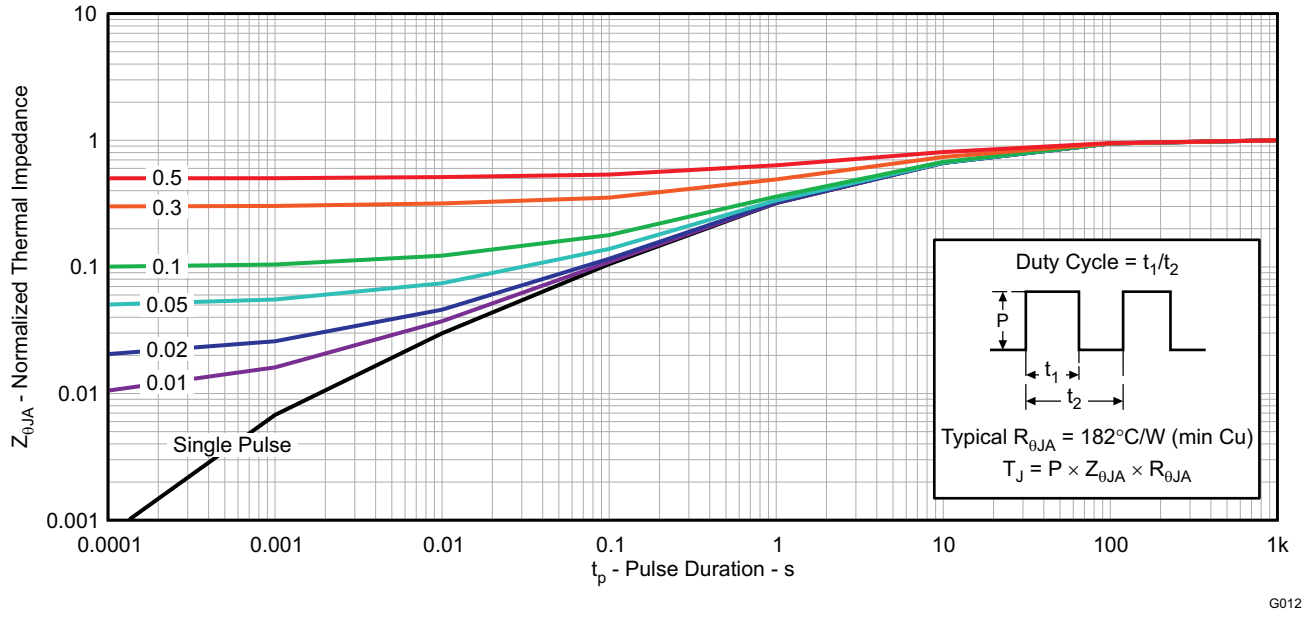


Figure 1. Transient Thermal Impedance

TYPICAL MOSFET CHARACTERISTICS (continued)

(T_A = 25°C unless otherwise stated)

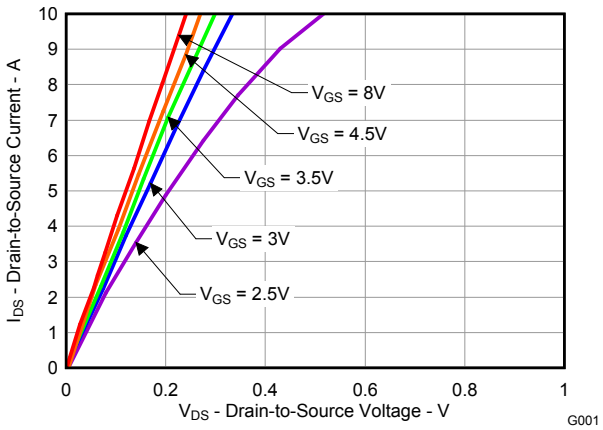


Figure 2. Saturation Characteristics

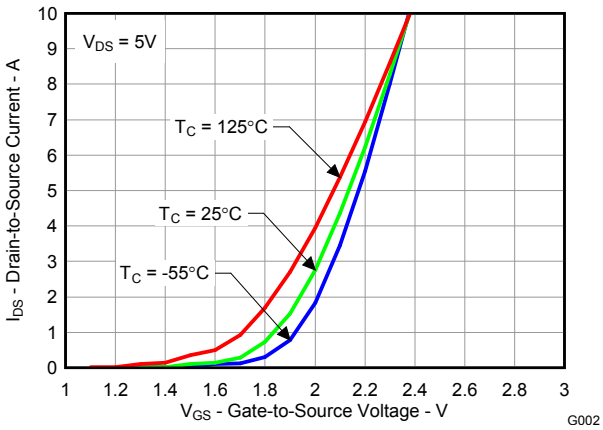


Figure 3. Transfer Characteristics

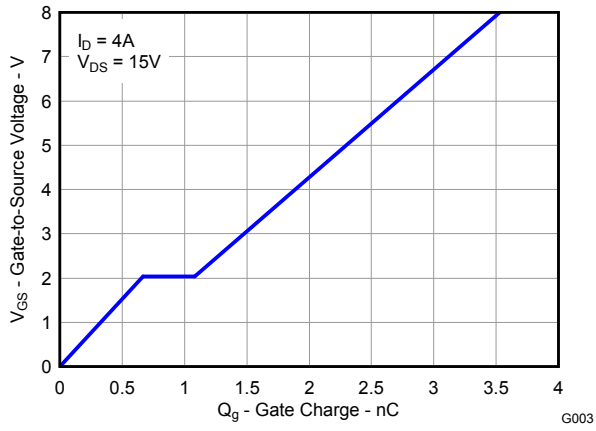


Figure 4. Gate Charge

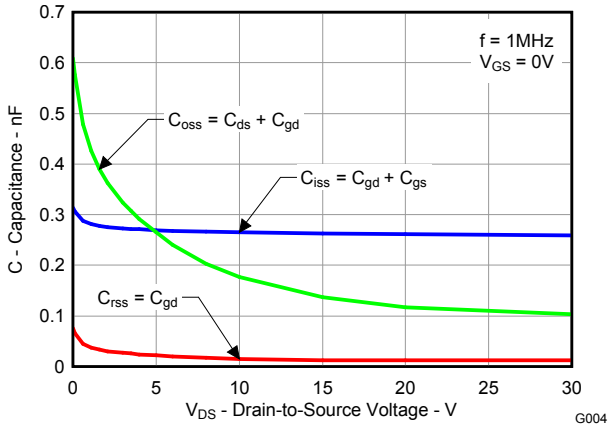


Figure 5. Capacitance

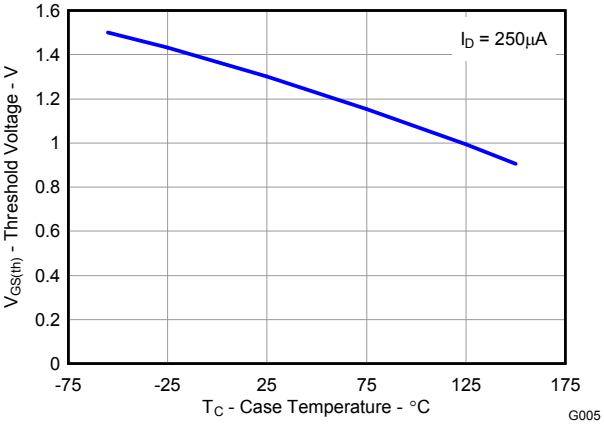


Figure 6. Threshold Voltage vs. Temperature

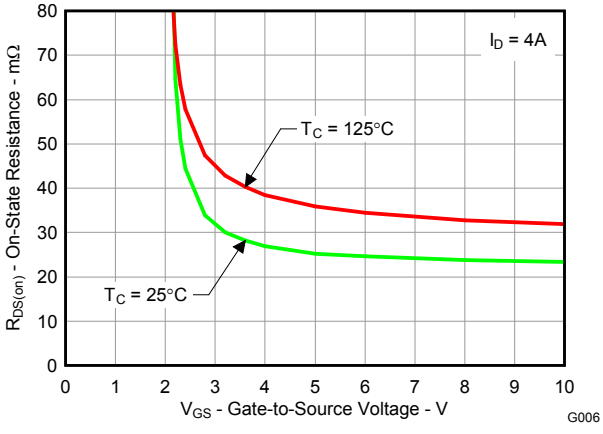


Figure 7. On-State Resistance vs. Gate-to-Source Voltage

TYPICAL MOSFET CHARACTERISTICS (continued)

(T_A = 25°C unless otherwise stated)

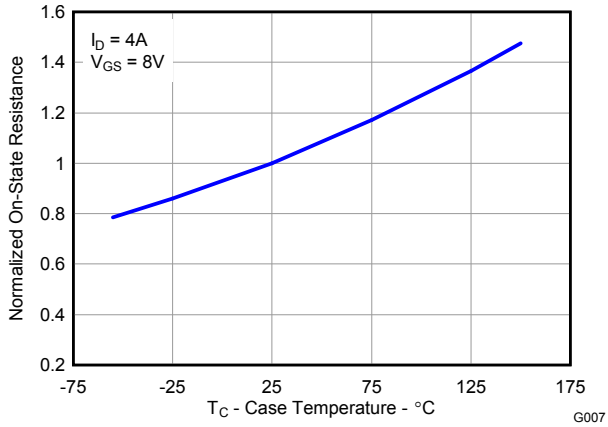


Figure 8. Normalized On-State Resistance vs. Temperature

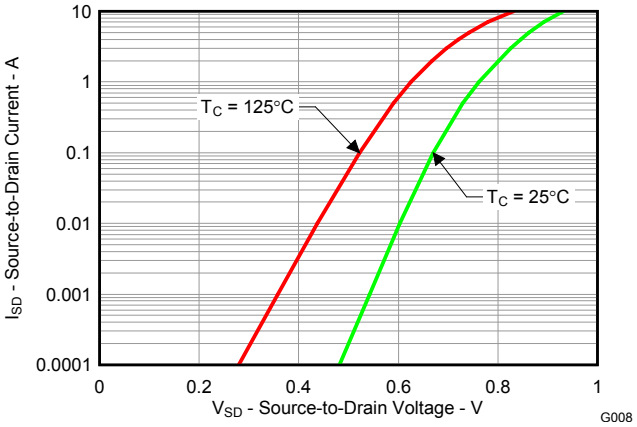


Figure 9. Typical Diode Forward Voltage

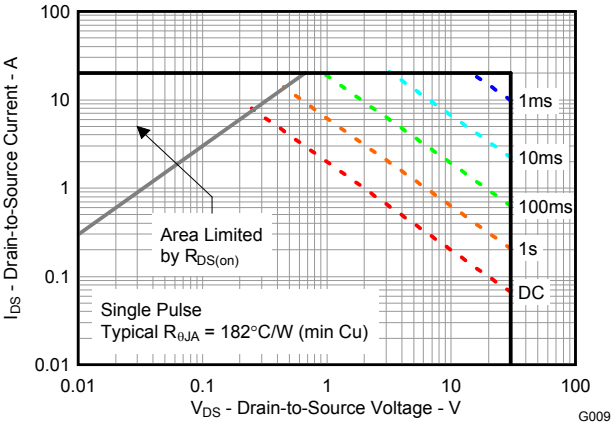


Figure 10. Maximum Safe Operating Area

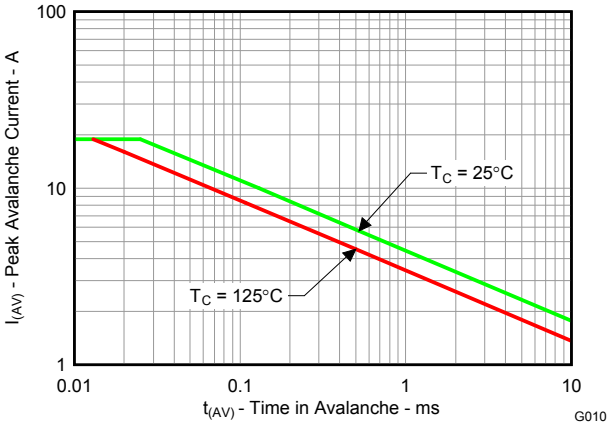


Figure 11. Single Pulse Unclamped Inductive Switching

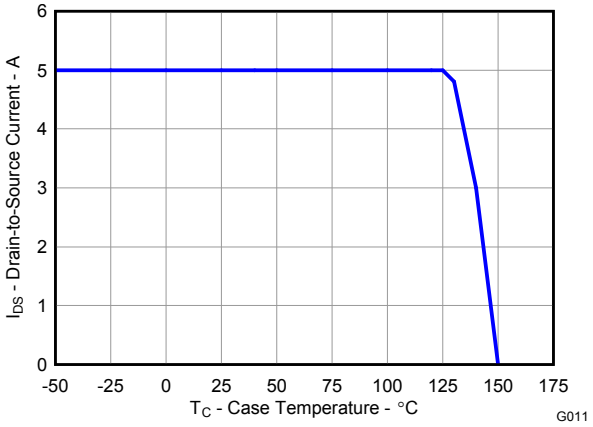
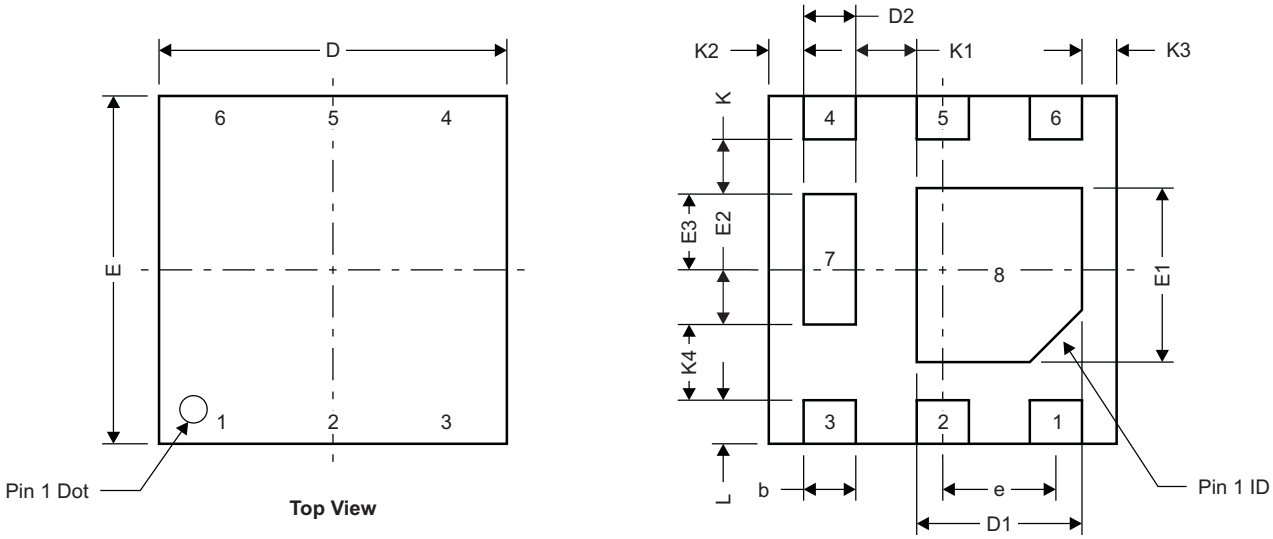


Figure 12. Maximum Drain Current vs. Temperature

MECHANICAL DATA

Q2 Package Dimensions

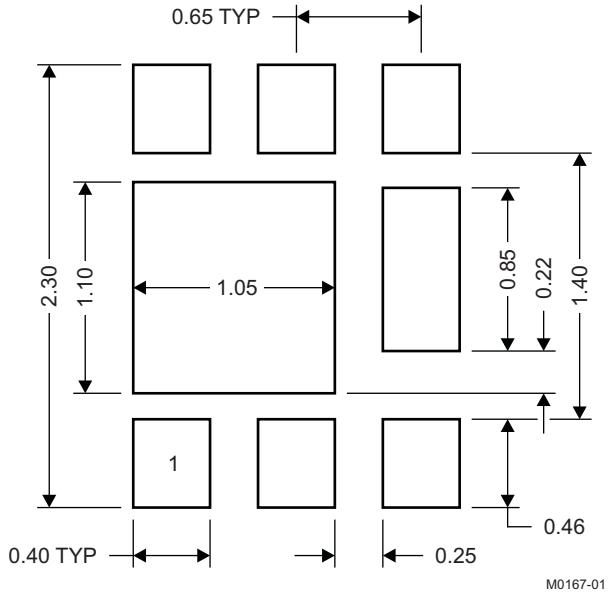


Pinout	
Source	4, 7
Gate	3
Drain	1, 2, 5, 6, 8

M0175-02

DIM	MILLIMETERS			INCHES		
	MIN	NOM	MAX	MIN	NOM	MAX
A	0.700	0.750	0.800	0.028	0.030	0.032
A1	0.000		0.050	0.000		0.002
b	0.250	0.300	0.350	0.010	0.012	0.014
C	0.203 TYP			0.008 TYP		
D	2.000 TYP			0.080 TYP		
D1	0.900	0.950	1.000	0.036	0.038	0.040
D2	0.300 TYP			0.012 TYP		
E	2.000 TYP			0.080 TYP		
E1	0.900	1.000	1.100	0.036	0.040	0.044
E2	0.280 TYP			0.0112 TYP		
E3	0.470 TYP			0.0188 TYP		
e	0.650 BSC			0.026 TYP		
K	0.280 TYP			0.0112 TYP		
K1	0.350 TYP			0.014 TYP		
K2	0.200 TYP			0.008 TYP		
K3	0.200 TYP			0.008 TYP		
K4	0.470 TYP			0.0188 TYP		
L	0.200	0.25	0.300	0.008	0.010	0.012

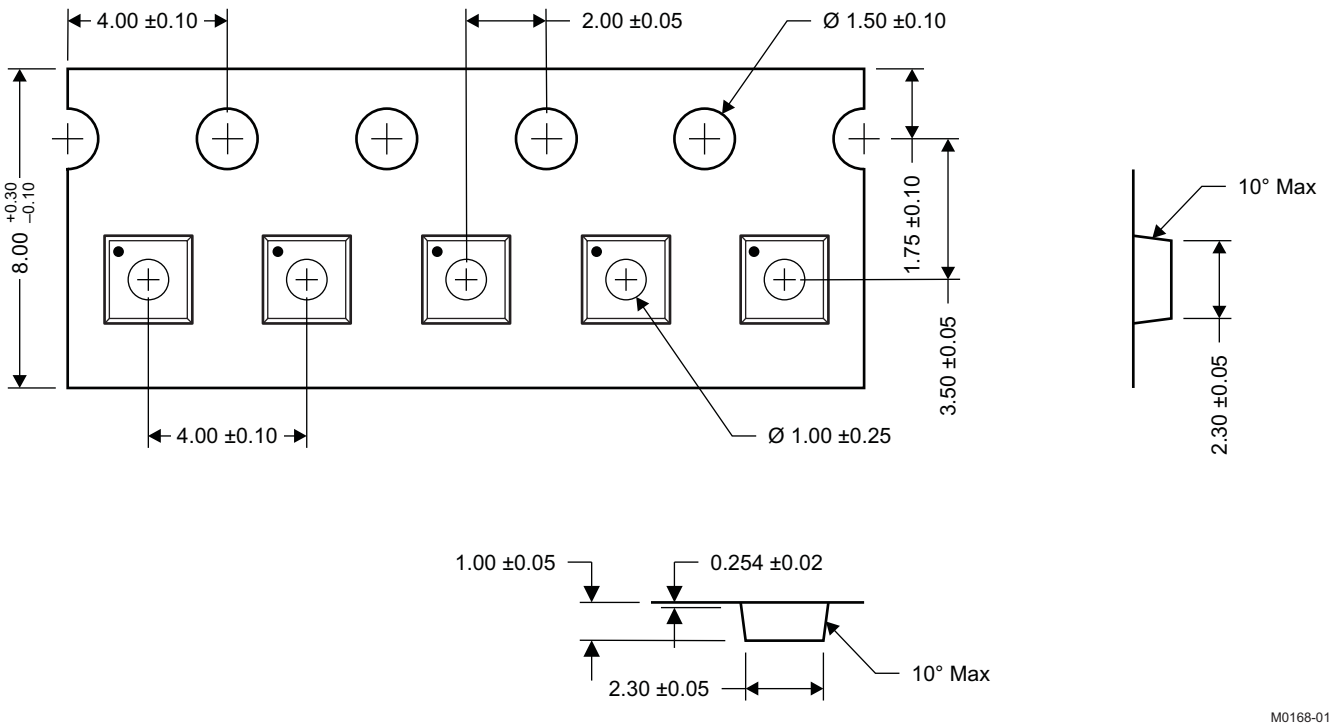
Recommended PCB Pattern



Note: All dimensions are in mm, unless otherwise specified.

For recommended circuit layout for PCB designs, see application note SLPA005 – ***Reducing Ringing through PCB Layout Techniques***.

Q2 Tape and Reel Information



Notes:
1. Measured from centerline of sprocket hole to centerline of pocket
2. Cumulative tolerance of 10 sprocket holes is ±0.20
3. Other material available
4. Typical SR of form tape Max 10^8 OHM/SQ
5. All dimensions are in mm, unless otherwise specified.

REVISION HISTORY

Changes from Original (March 2010) to Revision A	Page
• Changed Q_{rr} - Reverse Recovery Charge From: 10.2 nC To: 6.4 nC	2

Changes from Revision A (March 2010) to Revision B	Page
• Deleted the Package Marking Information section	8

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